

## IN THE SPECIFICATION

Following is a marked-up version of each amended paragraph of the subject patent application. The Examiner is requested to delete the indicated paragraph and replace it with the amended paragraph. The location for each of the deleted and replaced paragraphs is also indicated.

Replace paragraph [0007] with the following.

[0007] An example of a prior art dual damascene process is illustrated in the cross-sectional views of Figures 1A-1C during various stages of fabrication. As depicted in Figure 1A, a dielectric layer 10 is deposited or formed on a lower level interconnect 12. A photoresist layer 16, formed over the dielectric layer 10, is patterned and etched according to conventional techniques to form an opening 18 therein. An anisotropic etch process etches a via hole or window 20 in the dielectric layer 10 through the opening 18. The photoresist layer 16 is removed and replaced by a photoresist layer 30 (see Figure 1B) that is then patterned and etched to form a trench pattern 32. An anisotropic etch process forms a trench 34 (extending perpendicular to the plane of the paper) and simultaneously extends the opening 18 to an upper surface 36 of the lower level interconnect 12. The hole or window 20 can be formed to stop on the upper surface 36 and expose the lower level interconnect 12 (as shown in Figure 1B) or alternatively can be over-etched to extend partially into the lower level interconnect 12.

Replace paragraph [0016] with the following.

[0016] Figures 4A and 4B illustrates a prior art flip-chip integrated circuit device structures.

Replace paragraph [0024] with the following.

[0024] The bond pads are formed by depositing a metal barrier layer, typically tantalum-nitride, tantalum or titanium nitride, followed by an aluminum layer on an upper surface of the integrated circuit. The aluminum layer undergoes conventional masking, patterning, and etching ~~etchings~~ steps to define the aluminum bond pads. In one embodiment, an antireflective coating layer is disposed over the aluminum layer to reduce aluminum reflections during the photolithographic process. A material of the antireflective coating layer comprises titanium-nitride or silicon oxynitride. The bond pads are connected to one or more underlying interconnect structures

or circuit elements through underlying conductive vias. For those devices in which the interconnect structures are formed from copper, such as by the damascene process described above, the bond pads are conventionally formed of aluminum, as it is known that the gold wires adhere poorly to a copper bond pad.